AMENDMENTS TO THE SPECIFICATION:

Please replace the paragraph beginning on page 5, line 15, and ending on page 6,

line 7, with the following amended paragraph:

Recently, many attempts have been made to use the OTFT for various drive

devices. However, to realize the practical use of OTFT in LCD or flexible displays

using organic EL, not only should a charge mobility increase to the level of 5 cm²•V

¹•sec⁻¹ or higher, but also improvement in the driving and threshold voltages of the

device should be achieved. In particular, for simplifying the preparation and reducing

the cost, it can be desirable for the whole process of preparing the OTFT to be

carried out by an all-printing or all-spin method on a plastic substrate. Under the

circumstances, there have been many researches research efforts for developing a

method to simplify the preparation of the organic gate insulating film and to increase

the charge mobility in the interface between the insulator and the organic active

layer. However, satisfactory results have yet to be obtained.

Please replace the paragraph beginning on page 6, line 15, and ending on page 6,

line 24, with the following amended paragraph:

The present inventors devoted much effort to meet these demands and found

that, when using a multi-layered gate insulator including a first layer of a high K k

material and a second layer of an insulating polymer being compatible with an

organic active layer and positioned directly beneath the organic active layer, the

OTFT thus obtained exhibits a higher charge mobility and a lower driving and

threshold voltages and its whole preparation can be achieved by a wet process, such

as printing or spin coating.

Page 3

Please replace the paragraph beginning on page 8, line 19, and ending on page 8,

line 21, with the following amended paragraph:

As mentioned above, the layering order between the organic active layer and

the source/drain electrode may be changed relative to each other.

Please replace the paragraph beginning on page 9, line 6, and ending on page 10,

line 3, with the following amended paragraph:

In the present invention, the first layer of the gate insulating film is composed

of a high k material having both high dielectric constant (k) and excellent insulating

properties, and it is formed by a wet process. Specifically, the first insulating layer 2

is made of (1) a mixture of an insulating organic polymer and an organic metal

compound having a dielectric constant of 5 or higher, or (2) a mixture of an insulating

organic polymer and nanoparticles of an inorganic metal oxide or ferroelectric

insulator having a dielectric constant of 5 or more. The dielectric constant 'k' of the

first layer can be adjusted by controlling a weight ratio between the organic polymer

and the organic metal compound or the nanoparticles. The dielectric constant of the

first insulating layer should be controlled at 5 or higher and, in the case of the

dielectric constant being less than 5, an improvement of drive properties cannot be

achieved is more difficult to achieve due to the lower effective dielectric constant. For

formation of the first layer, the mixture is coated on the substrate including the gate

electrode by the wet process, and then baked.

Please replace the paragraph beginning on page 20, line 11, and ending on page 20,

line 23, with the following amended paragraph:

According to the preferable embodiment of the present invention, the OTFT

can be prepared by a process comprising the steps of: providing the gate electrode

disposed on the substrate and forming a first layer of a high K k material, a second

layer of an organic insulating polymer compatible with the organic active layer, the

organic active layer and the source/drain electrode sequentially, wherein the first and

the second layer is disposed through a wet process such as spin coating, the second

layer is positioned directly beneath the organic active layer and the layering order

between the organic active layer and the source/drain can be reversed.